

Esp 2811  
0819-425

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Haruko INOUE et al. )  
Serial No. 09/666,156 ) Art Unit: 2811  
Filed: September 19, 2000 ) Examiner: Unas  
For: HIGH-VOLTAGE MOS )  
TRANSISTOR AND METHOD FOR )  
FABRICATING THE SAME )



INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the reference(s) listed on the attached Form PTO-1449 be made of record in the above-identified application. Copies of the references are submitted herewith in accordance with 37 C.F.R. 1.98(a).

Inasmuch these references are being submitted before the issuance of a first Action on the merits of the case, and further, within three months of the filing date of the application, no fee is required.

The Commissioner is hereby authorized to charge any deficiencies fees or to credit any overpayments to counsel's Deposit Account No. 19-2380. A duplicate copy of this sheet is attached.

Respectfully submitted,

  
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